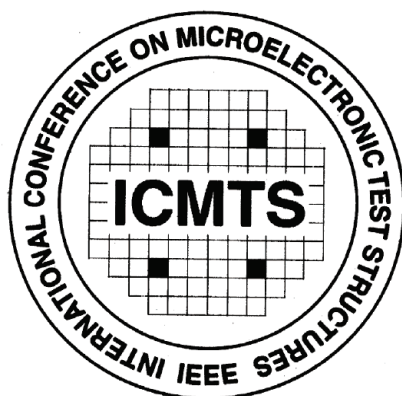


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Welcome Letter

Dear Colleagues,

The 2013 International Conference on Microelectronic Test Structures (ICMTS 2013) will be held at Osaka University Nakanoshima Center, Osaka in Japan. This is the 26th anniversary of the ICMTS and the 8th conference to be held in Japan.

Test structure is key characterization vehicle for process development, device development, circuit design and its production and its importance is increasing. ICMTS has brought engineers and researchers to discuss recent development and future directions of test structure over the past two decades. Topics of ICMTS have been expanded as semiconductor technologies and application advance. They include material and process characterization, replicated feature metrology, manufacturing of integrated circuits, reliability and product failure analysis, characterization of Memory, MEMS, sensors, RF or Power IC, Si or Organic devices, Capacitance, 3D structure with TSV & circuit modeling, parameter extraction, variability, yield enhancement, production process control, etc.

The ICMTS 2013 consists of 40 papers in 10 oral sessions. Details of the sessions are described in this program. I believe all papers turn on your interest and help your work. The sessions will be preceded by a one-day Tutorial Short Course on microelectronic test structure and there will be an equipment exhibition in parallel with the sessions.

Osaka is a historical city in Japan and includes Osaka Castle with beautiful Golden Tea Room and a lot of nice foods. You will be able to enjoy some Osaka foods and many Cherry blossoms on March. Osaka University Nakanoshima Center is very easy access from hotels and you can easily visit most of historical place, shopping and food area. I'm sure that everyone will get benefit by attending the various sessions and also enjoy Osaka. For further information, please visit the ICMTS web site at <http://www.if.t.u-tokyo.ac.jp/ICMTS13/>.

I look forward seeing you at the ICMTS 2013 in Osaka.

Sincerely,

Tatsuya Ohguro
General Chairman

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